

**IN THE ABSTRACT:**

Please **AMEND** the abstract as follows (Exhibit II is a marked up version of the amended Abstract):

The present invention is related to a polycrystalline silicon film containing Ni which is formed by crystallizing an amorphous silicon layer containing nickel. The present invention includes a polycrystalline silicon film wherein the polycrystalline film contains Ni atoms of which density ranges from  $2 \times 10^{17}$  to  $5 \times 10^{19}$  atoms/cm<sup>3</sup> on average and comprises a plurality of needle-shaped silicon crystallites. In another aspect, the present invention includes a polycrystalline silicon film wherein the polycrystalline film contains Ni atoms of which density ranges from  $2 \times 10^{17}$  to  $5 \times 10^{19}$  atoms/cm<sup>3</sup>, comprises a plurality of needle-shaped silicon crystallites and is formed on an insulating substrate. Such a polysilicon film according to the present invention avoids metal contamination usually generated in a conventional method of metal induced crystallization.

**IN THE CLAIMS:**

Please **CANCEL** Claim 8 without prejudice or disclaimer of the underlying subject matter.

Please **AMEND** Claims 1, 3, 6 and 9 as follows (Exhibit III is a marked up version of the amended claims):

1. (Amended) A polycrystalline silicon film, the polycrystalline film containing Ni atoms of which density ranges  $2 \times 10^{17}$  to  $5 \times 10^{19}$  atoms/cm<sup>3</sup> on average, and an electrical conductivity activation energy between 0.52eV and 0.71eV, the polycrystalline silicon film comprising a plurality of needle-shaped silicon crystallites.